



## PE5080GS N-Channel Enhancement Mode Power MOSFET

### PE5080GS Description

The PE5080GS uses deep trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. It can be used in a wide variety of applications.

### PE5080GS General Features

- $V_{DS} = 100V$ ,  $I_D = 80A$

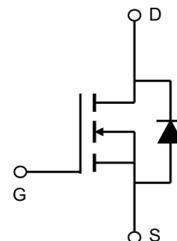
$R_{DS(ON)} < 7.7m\Omega$  @  $V_{GS}=10V$

$R_{DS(ON)} < 11.4m\Omega$  @  $V_{GS}=4.5V$

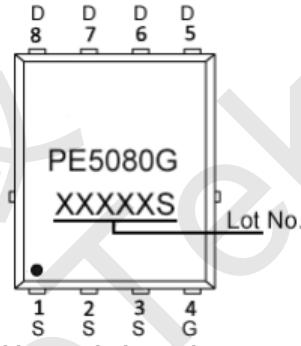
- High Power and current handing capability
- Lead free product is acquired

### PE5080GS Application

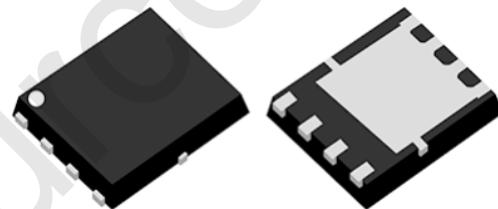
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



DFN5x6-8L

### PE5080GS Absolute Maximum Ratings ( $TC=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	80	A
Drain Current-Continuous ( $T_C=100^\circ C$ )	$I_D(T_C=100^\circ C)$	50	A
Pulsed Drain Current (Note 1)	$I_{DM}$	240	A
Maximum Power Dissipation	$P_D$	52	W
Single Pulsed Avalanche Energy ( $L=0.5mH$ )	$E_{AS}$	144	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### PE5080GS Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.4	°C/W
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**PE5080GS Electrical Characteristics (TC=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=80V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.3	2	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	6.4	7.7	$m\Omega$
		$V_{GS}=4.5V, I_D=15A$	-	9.2	11.4	$m\Omega$
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V, F=1.0MHz$	-	2945	-	pF
Output Capacitance	$C_{oss}$		-	737	-	pF
Reverse Transfer Capacitance (Note 4)	$C_{rss}$		-	2	-	pF
Gate Resistance	$R_g$	$V_{DS}=0V, V_{GS}=0V, F=1.0MHz$	-	3.2	-	$\Omega$
<b>Switching Characteristics</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS}=50V, I_D=13A, V_{GS}=10V, R_G=6\Omega$	-	14	-	nS
Turn-on Rise Time	$t_r$		-	28.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	46.5	-	nS
Turn-Off Fall Time	$t_f$		-	42.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=13A, V_{GS}=10V$	-	39.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	6.6	-	nC
Gate-Drain Charge	$Q_{gd}$		-	8.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Maximum Body-Diode Continuous Current	$I_s$				63	A
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_s=10A$	-	-	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F=13A, di/dt=100A/\mu s$		177		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			1291		nC

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to product.



### PE5080GS Typical Electrical and Thermal Characteristics

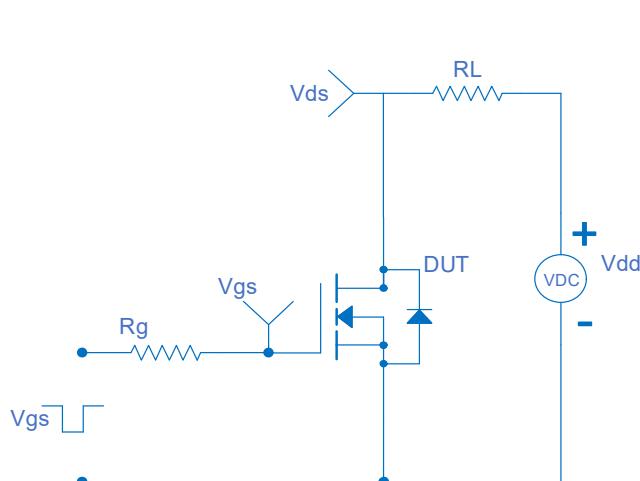


Figure 1 Switching Test Circuit

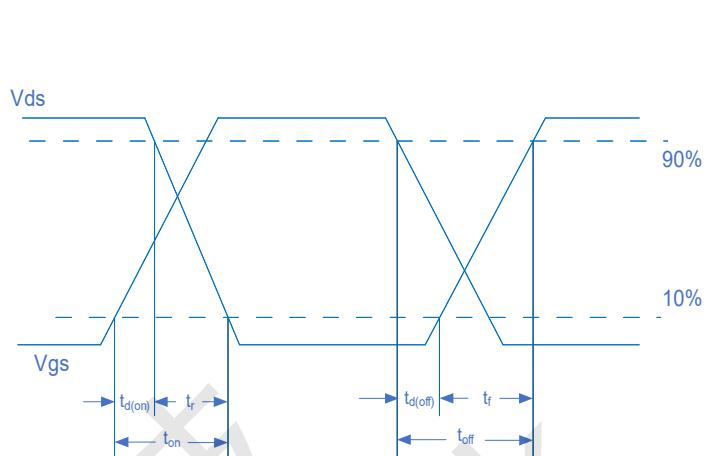


Figure 2 Switching Waveform

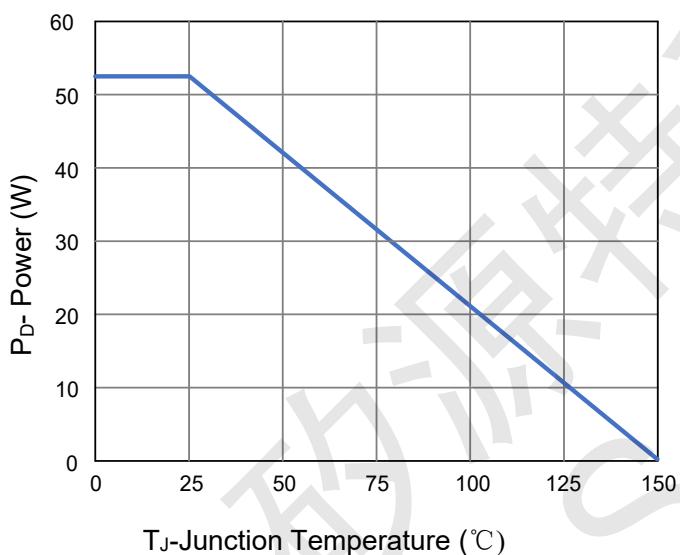


Figure 3 Power De-rating

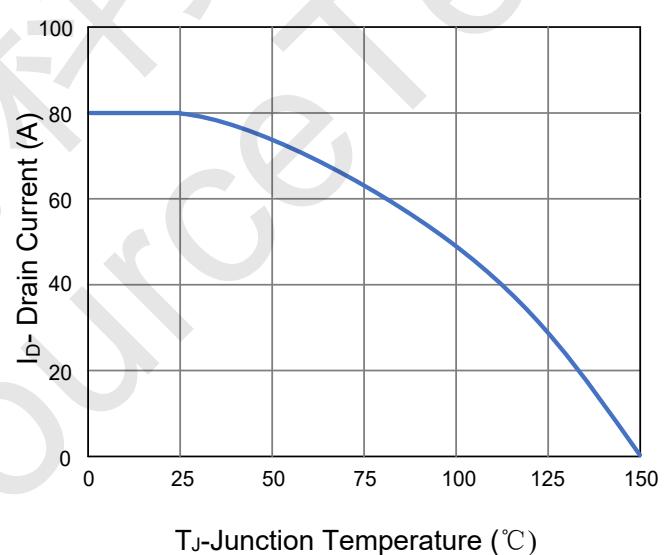


Figure 4 Drain Current

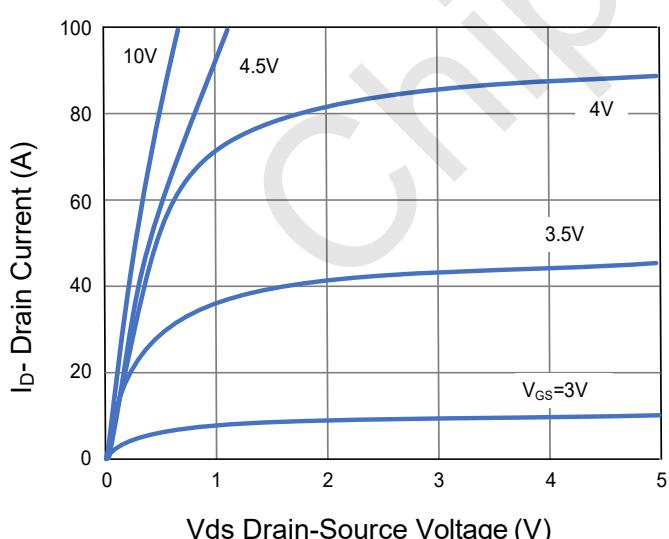


Figure 5 Output Characteristics

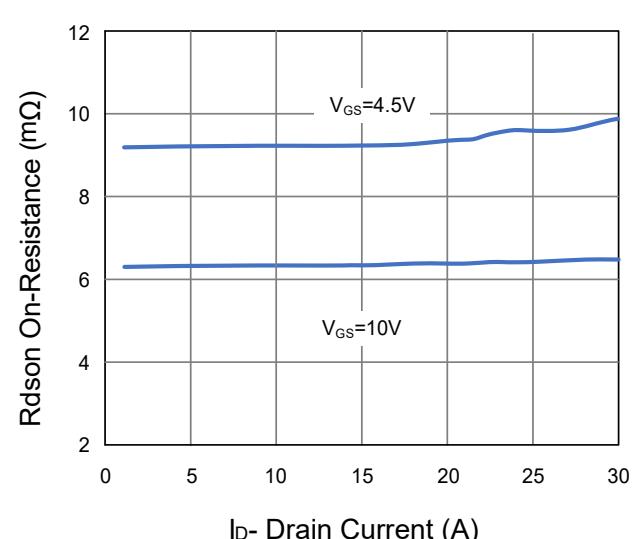


Figure 6 Rdson vs Drain Current

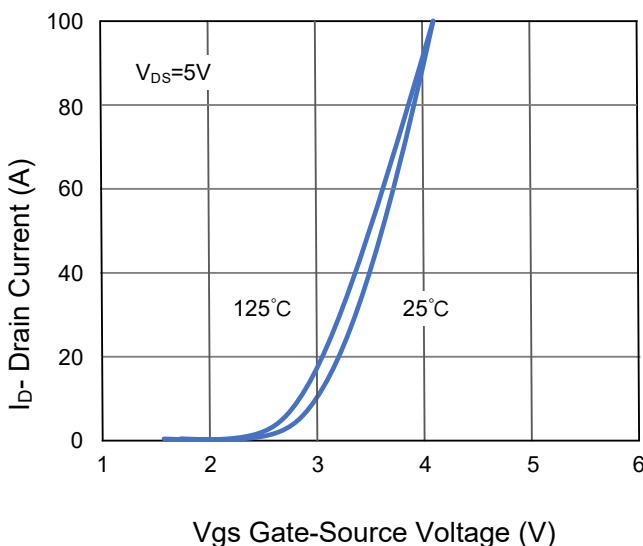


Figure 7 Transfer Characteristics

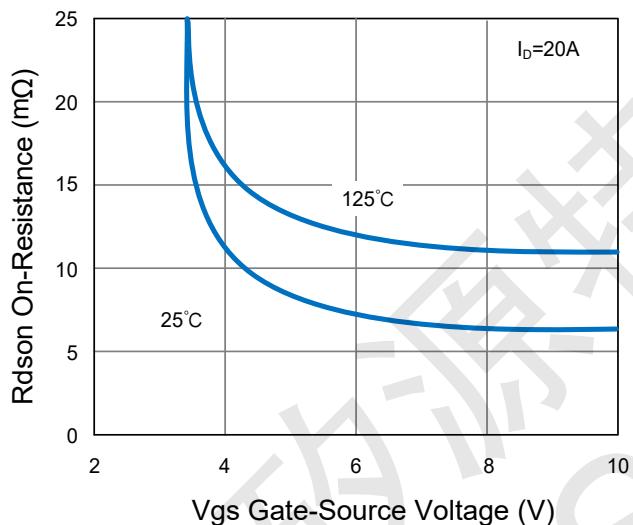


Figure 9  $R_{DSON}$  vs  $V_{GS}$

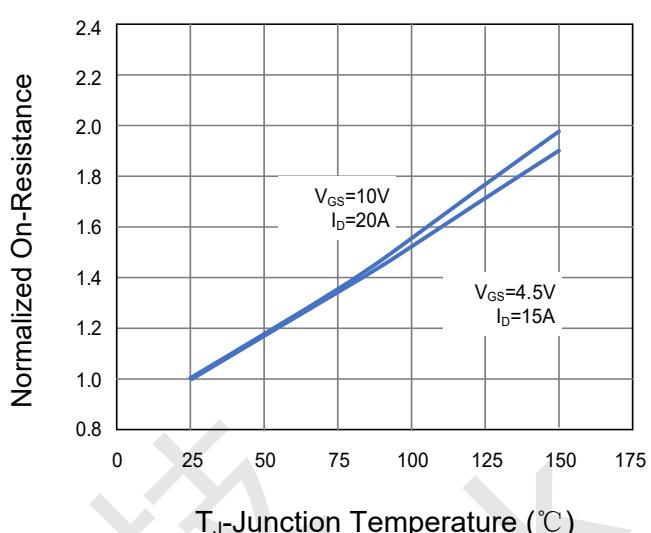


Figure 8  $R_{DSON}$  vs Junction Temperature

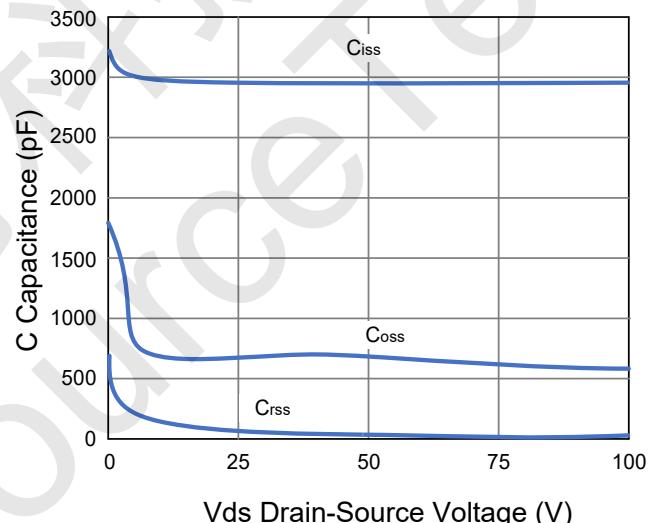


Figure 10 Capacitance vs  $V_{DS}$

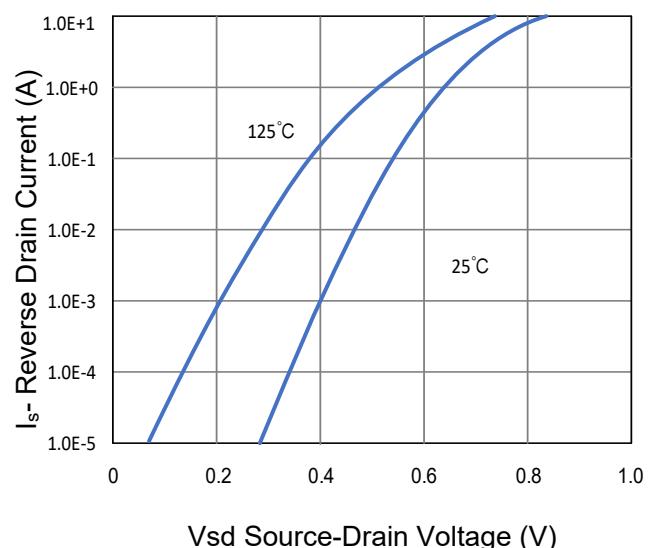


Figure 11 Gate Charge

Figure 12 Source- Drain Diode Forward

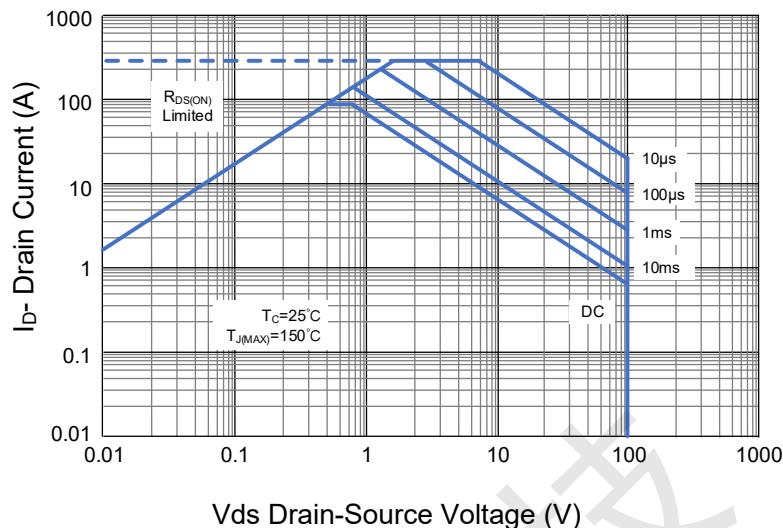


Figure 13 Safe Operation Area

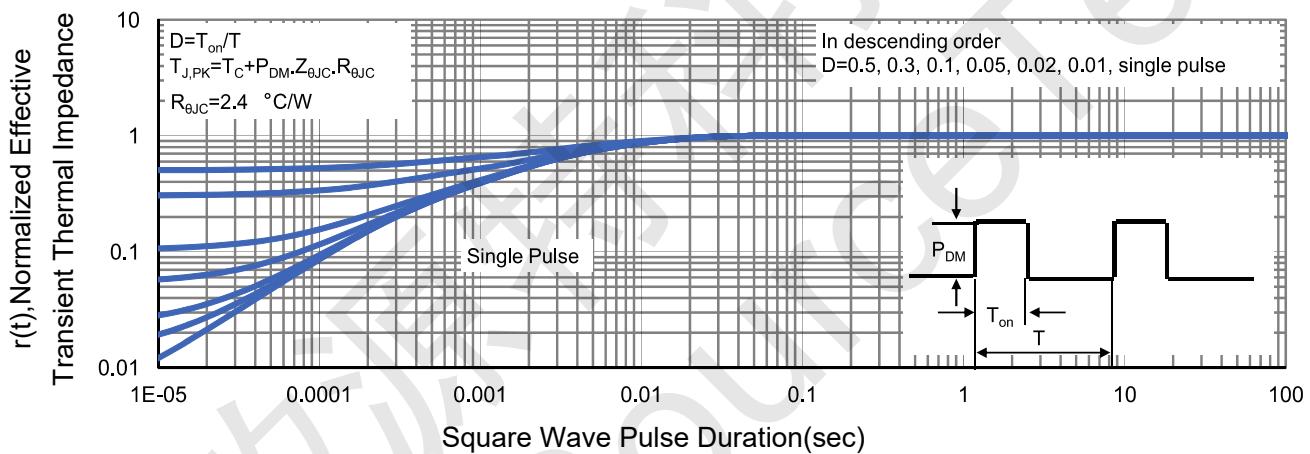
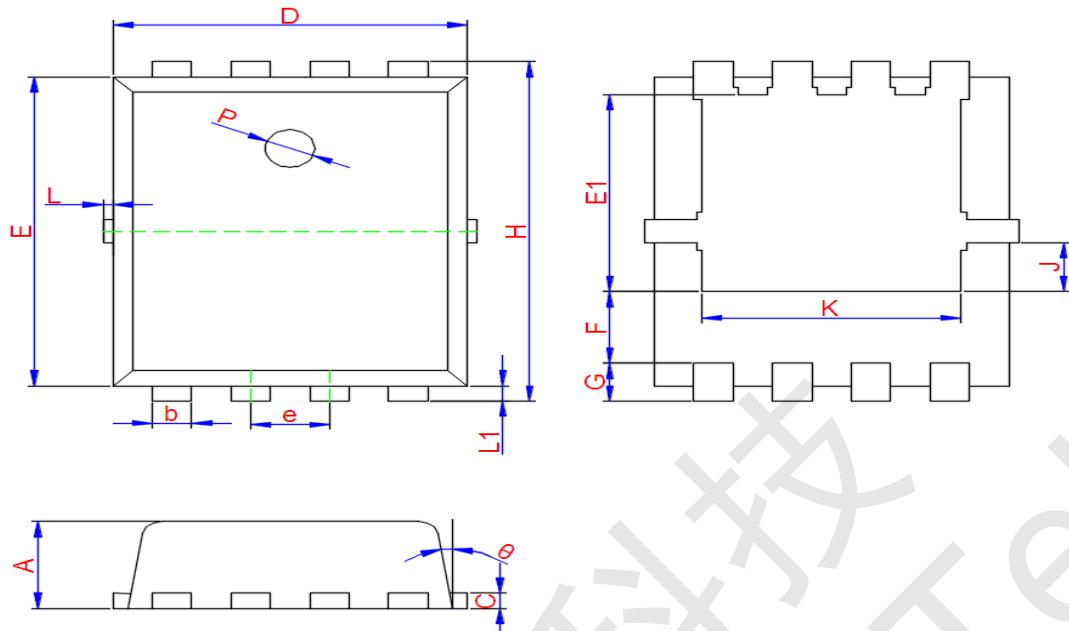


Figure 14 Normalized Maximum Transient Thermal Impedance



## PE5080GS DFN5x6-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.800	1.050	1.200
b	0.250	0.350	0.490
c	0.254TYP.		
D	4.800	5.000	5.100
e	1.270TYP.		
E	5.650	5.800	5.900
E1	3.400TYP.		
F	1.300TYP.		
G	0.600TYP.		
H	5.950	6.080	6.200
J	0.950TYP.		
K	4.000TYP		
L	-	-	0.150
L1	0.100	0.140	0.180
P	1.180TYP.		
θ	6°	10°	14°